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Color Code:

Red – Plasma Etching

Blue – Advanced Devices

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<http://patft.uspto.gov/netahtml/srchnum.htm>

US Patent Nr.	Title	Assignee	Filed	Date of Patent
6,680,232	Trench etch with incremental oxygen flow	Fairchild Semiconductor Corporation	9/19/01	1/20/04
6,680,233	Semiconductor device formed with disposable spacer and liner using high-K material and method of fabrication	Advanced Micro Devices, Inc.	10/9/01	1/20/04
6,680,255	Plasma etching methods	Micron Technology, Inc	10/29/99	1/20/04
6,682,657	Three dimensional etching process	Qinetiq Limited	7/17/97	1/27/04
6,682,965	Method of forming n-and p- channel field effect transistors on the same silicon layer having a strain effect	Sony Corporation	3/26/98	1/27/04
6,682,994	Methods for transistor gate formation using gate sidewall implantation	Texas Instruments Incorporated	4/16/02	1/27/04

6,686,558	Atmospheric pressure inductive plasma apparatus	TimeDomain CVD, Inc.	1/23/01	2/3/04
6,686,637	Gate structure with independently tailored vertical doping profile	International Business Machines Corporation	11/21/02	2/3/04
6,689,650	Fin field effect transistor with self-aligned gate	International Business Machines Corporation	9/27/01	2/10/04
6,689,702	High dielectric constant metal oxide gate dielectrics	Intel Corporation	11/25/02	2/10/04
6,693,333	Semiconductor-on-insulator circuit with multiple work functions	Advanced Micro Devices, Inc.	5/1/01	2/17/04